

FMI16N50ES

FUJI POWER MOSFET

Super FAP-E^{3S} series

N-CHANNEL SILICON POWER MOSFET

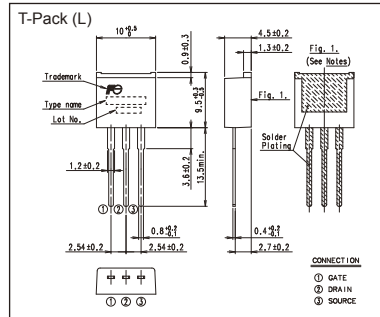
Features

- Maintains both low power loss and low noise
- Lower R_{DS(on)} characteristic
- More controllable switching dv/dt by gate resistance
- Smaller V_{GS} ringing waveform during switching
- Narrow band of the gate threshold voltage (4.2±0.5V)
- High avalanche durability

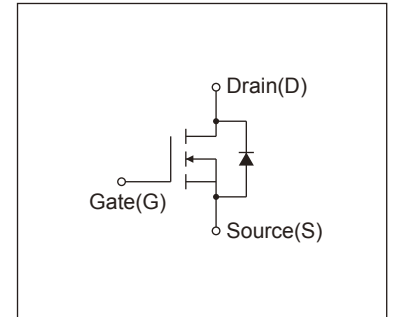
Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Outline Drawings [mm]



Equivalent circuit schematic



Maximum Ratings and Characteristics

Absolute Maximum Ratings at T_c=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V _{DS}	500	V	
	V _{DSSX}	500	V	V _{GS} = -30V
Continuous Drain Current	I _D	±16	A	
Pulsed Drain Current	I _{DP}	±64	A	
Gate-Source Voltage	V _{GS}	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I _{AR}	16	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E _{AS}	485	mJ	Note*2
Repetitive Maximum Avalanche Energy	E _{AR}	22.5	mJ	Note*3
Peak Diode Recovery dv/dt	dv/dt	4.8	kV/μs	Note*4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note*5
Maximum Power Dissipation	P _D	2.02	W	T _a =25°C
		225		T _c =25°C
Operating and Storage Temperature range	T _{ch}	150	°C	
	T _{stg}	-55 to + 150	°C	

Electrical Characteristics at T_c=25°C (unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	500	-	-	V
Gate Threshold Voltage	V _{GS} (th)	I _D =250μA, V _{DS} =V _{GS}	3.7	4.2	4.7	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V	-	-	25	μA
		V _{DS} =400V, V _{GS} =0V	-	-	250	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	10	100	nA
Drain-Source On-State Resistance	R _{DS} (on)	I _D =8A, V _{GS} =10V	-	0.33	0.38	Ω
Forward Transconductance	g _{fs}	I _D =8A, V _{DS} =25V	5.5	11	-	S
Input Capacitance	C _{iss}	V _{DS} =25V	-	1700	2550	pF
Output Capacitance	C _{oss}	V _{GS} =0V	-	210	315	
Reverse Transfer Capacitance	C _{rss}	f=1MHz	-	13	19.5	
Turn-On Time	td(on)	V _{cc} =300V	-	37	55.5	ns
	tr	V _{GS} =10V	-	30	45	
Turn-Off Time	td(off)	I _D =8A	-	87	130.5	
	tf	R _{GS} =18Ω	-	17	25.5	
Total Gate Charge	Q _G	V _{cc} =250V	-	48	72	nC
Gate-Source Charge	Q _{GS}	I _D =16A	-	17	25.5	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V	-	18	27	
Gate-Drain Crossover Charge	Q _{SW}		-	7	10.5	
Avalanche Capability	I _{AV}	L=1.52mH, T _{ch} =25°C	16	-	-	A
Diode Forward On-Voltage	V _{SD}	I _F =16A, V _{GS} =0V, T _{ch} =25°C	-	0.90	1.35	V
Reverse Recovery Time	trr	I _F =16A, V _{GS} =0V	-	0.46	-	μs
Reverse Recovery Charge	Q _{rr}	-di/dt=100A/μs, T _{ch} =25°C	-	6.0	-	μC

Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	R _{th} (ch-c)	Channel to Case			0.560	°C/W
	R _{th} (ch-a)	Channel to Ambient			75.0	°C/W

Note *1 : T_{ch}≤150°C.

Note *2 : Stating T_{ch}=25°C, I_{AS}=7A, L=18.1mH, V_{cc}=50V, R_G=50Ω.

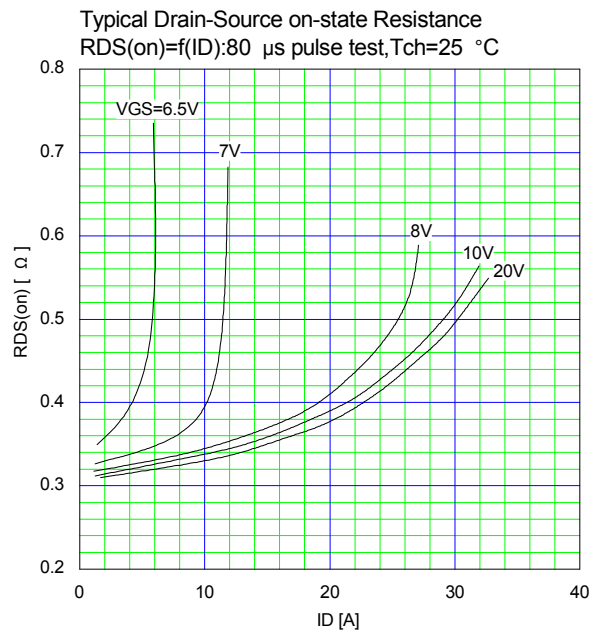
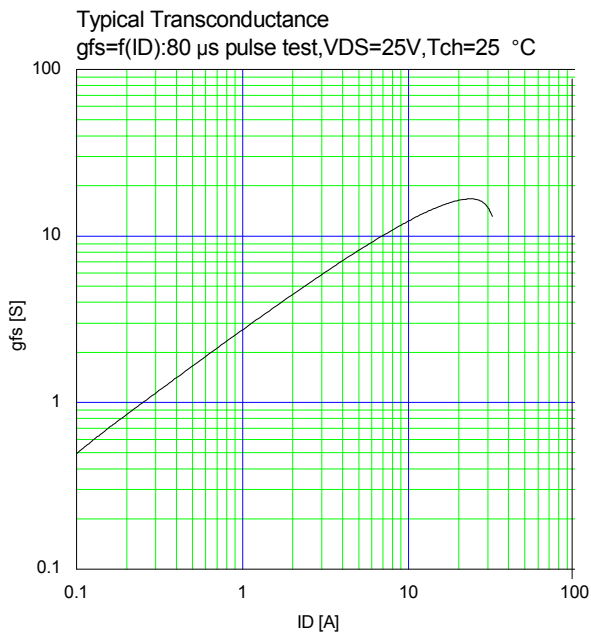
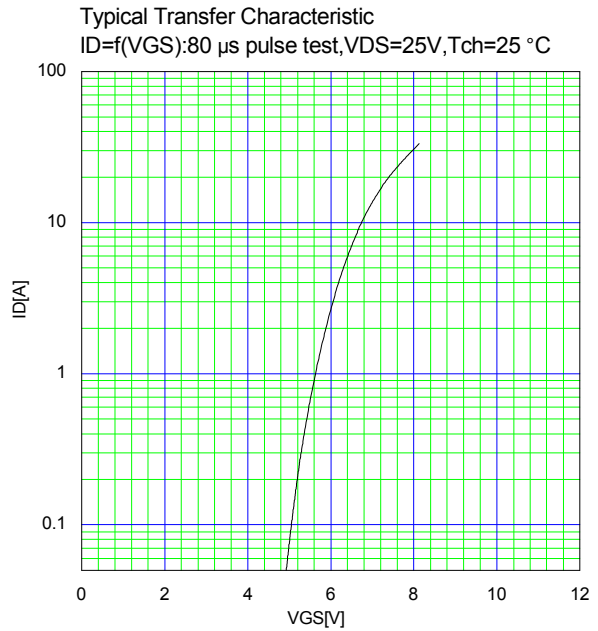
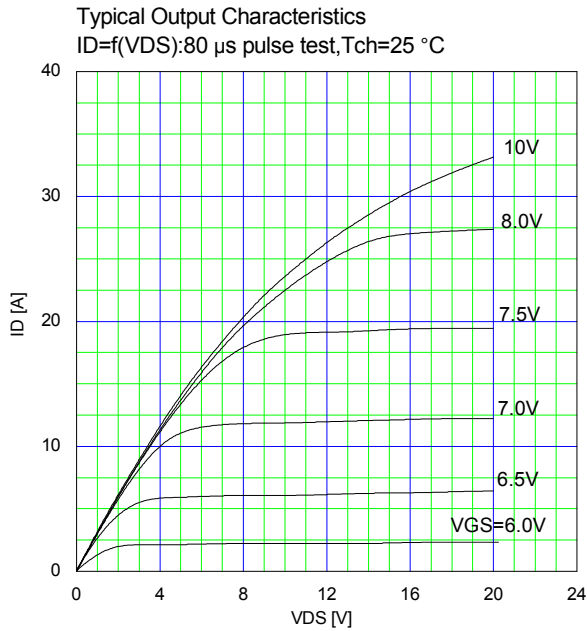
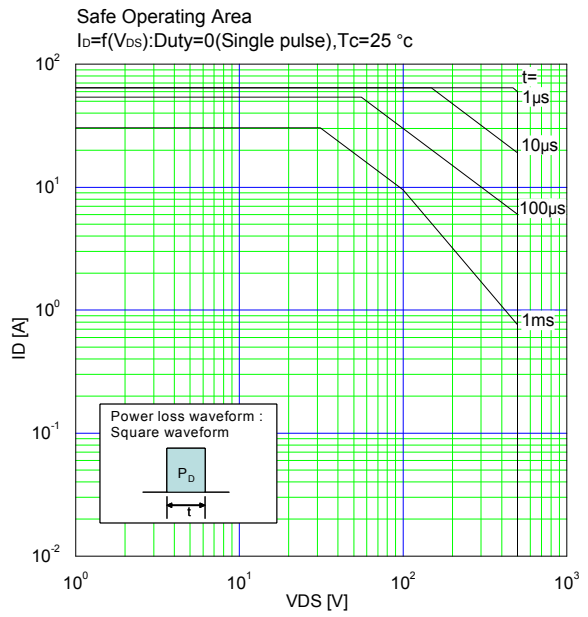
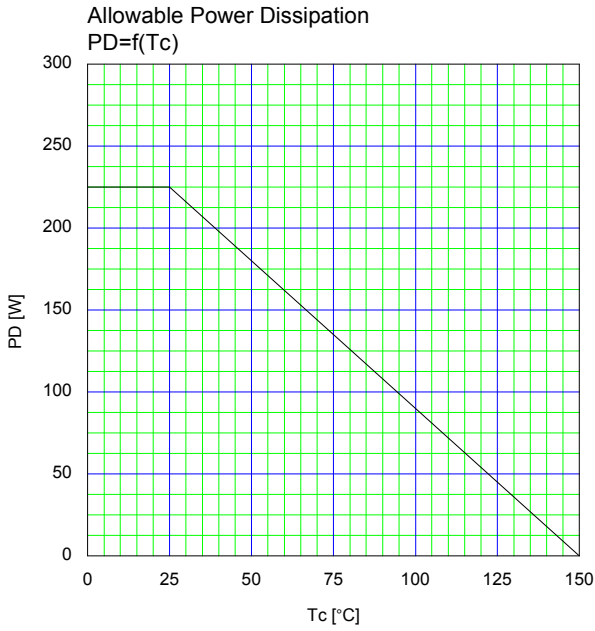
E_{AS} limited by maximum channel temperature and avalanche current.
See to 'Avalanche Energy' graph.

Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.

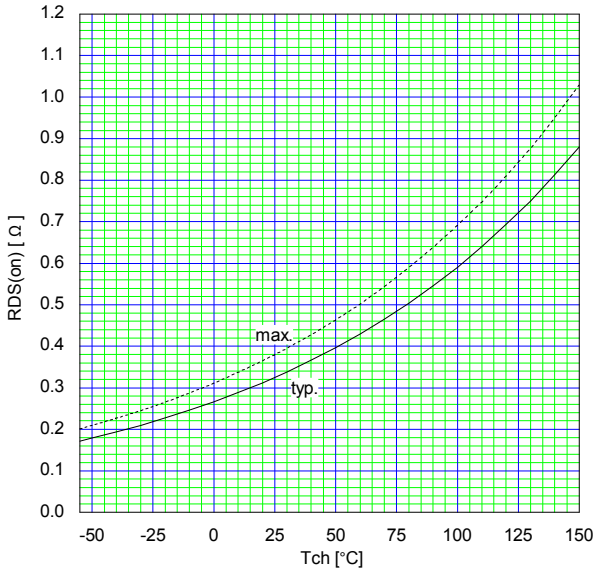
See to the 'Transient Thermal impedance' graph.

Note *4 : I_F≤-ID, -di/dt=100A/μs, V_{cc}≤BV_{DSS}, T_{ch}≤150°C.

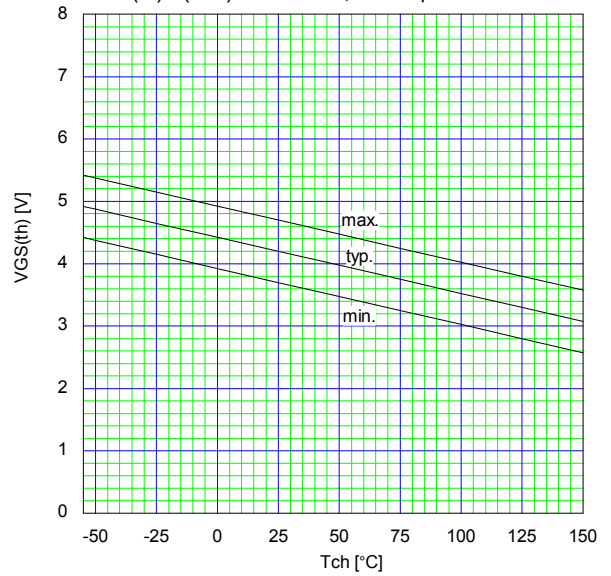
Note *5 : I_F≤-ID, dv/dt=4.8kV/μs, V_{cc}≤BV_{DSS}, T_{ch}≤150°C.



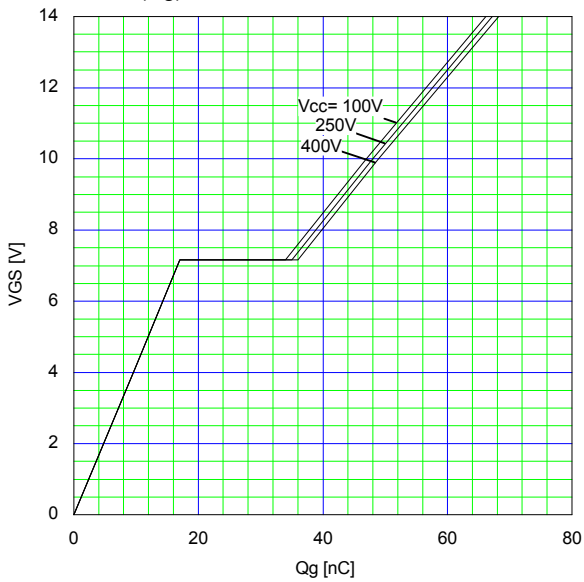
Drain-Source On-state Resistance
 $R_{DS(on)}=f(T_{ch}):I_D=8A, V_{GS}=10V$



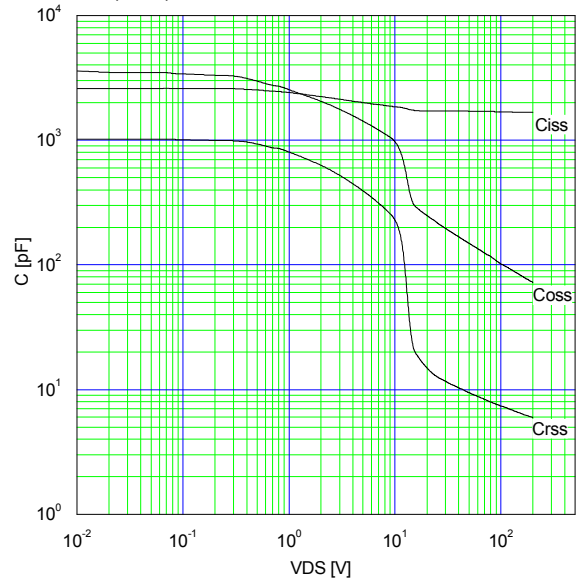
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



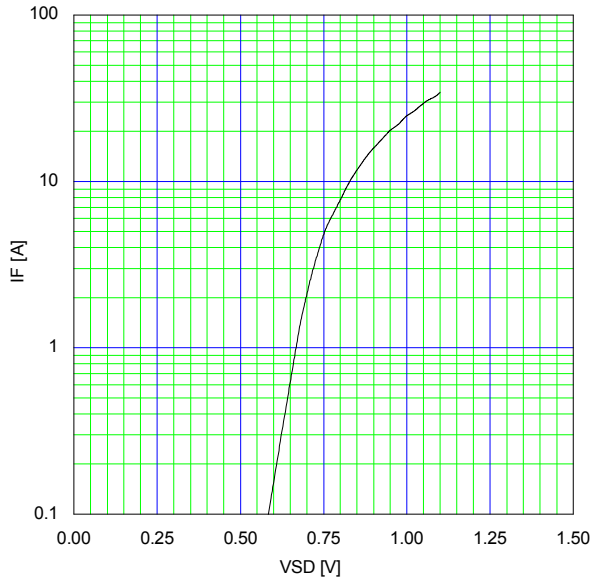
Typical Gate Charge Characteristics
 $V_{GS}=f(Q_g):I_D=16A, T_{ch}=25^\circ C$



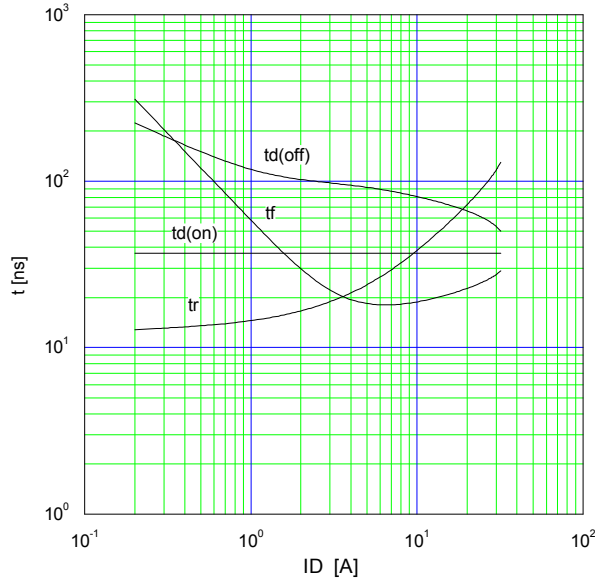
Typical Capacitance
 $C=f(V_{DS}):V_{GS}=0V, f=1MHz$



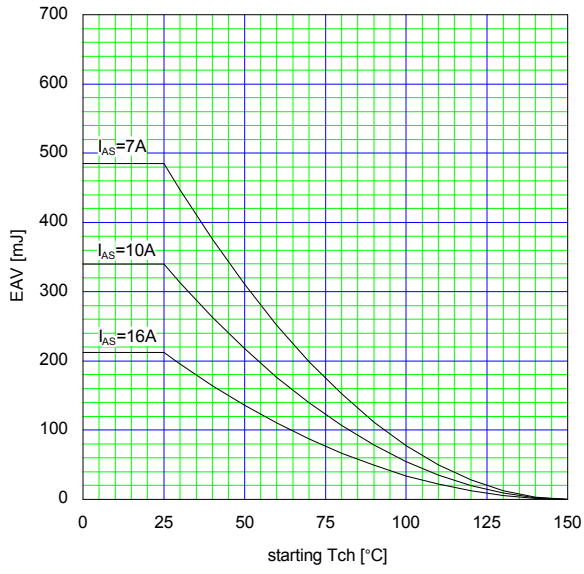
Typical Forward Characteristics of Reverse Diode
 $I_F=f(V_{SD}):80\mu s \text{ pulse test}, T_{ch}=25^\circ C$



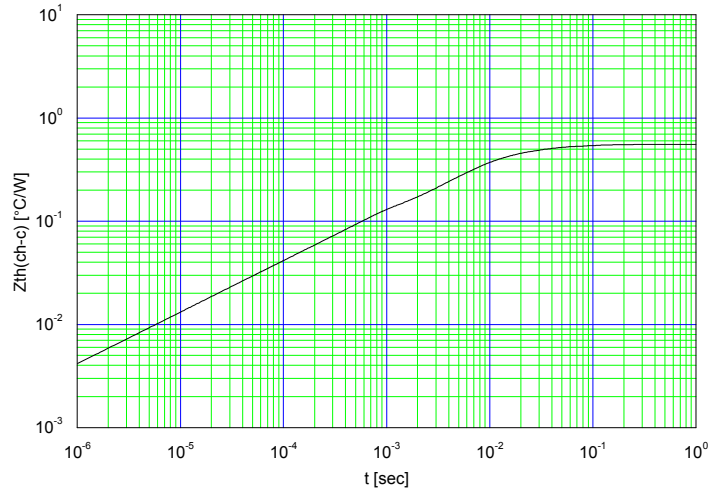
Typical Switching Characteristics vs. I_D
 $t=f(I_D):V_{cc}=300V, V_{GS}=10V, R_G=18\ \Omega$



Maximum Avalanche Energy vs. starting Tch
 $E(AV)=f(\text{starting Tch}):V_{cc}=50V, I(AV)\leq 16A$



Maximum Transient Thermal Impedance
 $Z_{th}(ch-c)=f(t):D=0$



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